



HFZT

SCHOTTKY BARRIER RECTIFIER

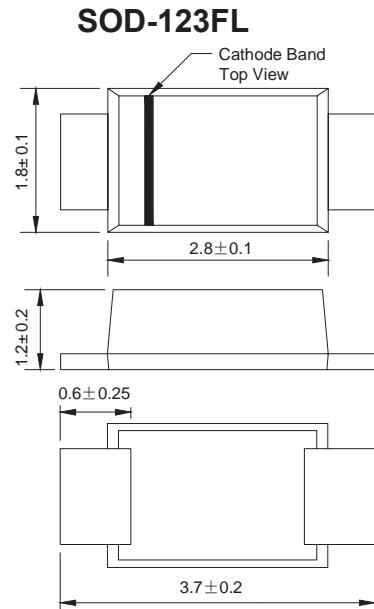
SS22---SS220
VOLTAGE RANGE: 20--- 200 V
CURRENT: 2.0 A

FEATURES

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: SOD-123FL
- Terminals: Solderable per MIL-STD-750, Method 2026
- Mounting Position: Any



Absolute Maximum Ratings and Electrical characteristics

@ 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	SS22	SS24	SS26	SS28	SS210	SS212	SS215	SS220	Units		
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	40	60	80	100	120	150	200	V		
Maximum RMS voltage	V_{RMS}	14	28	42	56	70	84	105	140	V		
Maximum DC Blocking Voltage	V_{DC}	20	40	60	80	100	120	150	200	V		
Maximum Average Forward Rectified Current	$I_{F(AV)}$	2.0							A			
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	50				40				A		
Max Instantaneous Forward Voltage at 2 A	V_F	0.55		0.70		0.85		0.95		V		
Maximum DC Reverse Current $T_a = 25^\circ C$ at Rated DC Reverse Voltage $T_a = 100^\circ C$	I_R	0.5 10		0.3 5						mA		
Typical Junction Capacitance ¹⁾	C_j	220		80						pF		
Operating Junction Temperature Range	T_j	-55 ~ +125							°C			
Storage Temperature Range	T_{stg}	-55 ~ +150							°C			

¹⁾Measured at 1MHz and applied reverse voltage of 4 V D.C.



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RATINGS AND CHARACTERISTIC CURVES

Fig.1 Forward Current Derating Curve

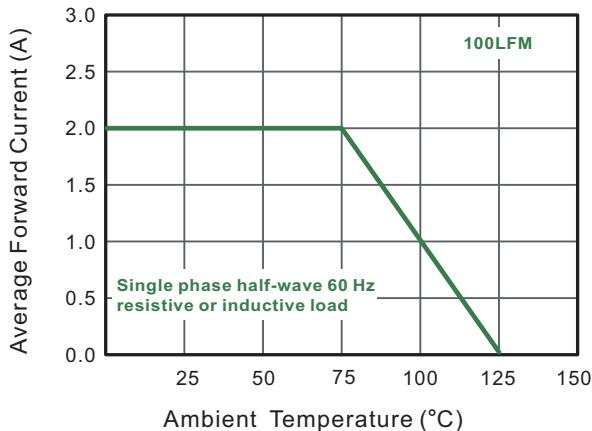


Fig.2 Typical Reverse Characteristics

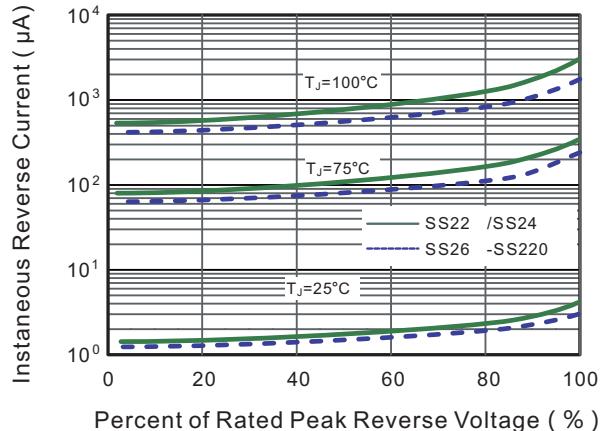


Fig.3 Typical Forward Characteristic

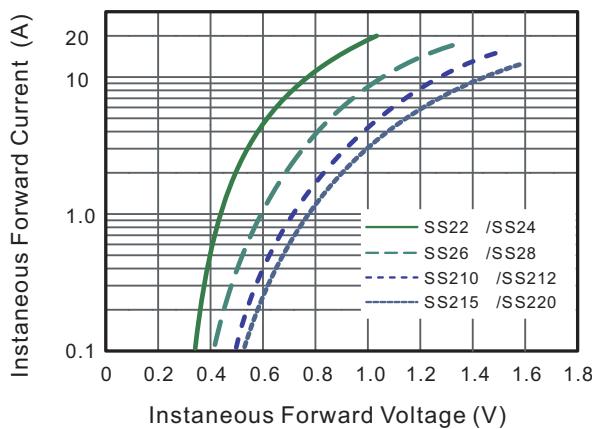


Fig.4 Typical Junction Capacitance

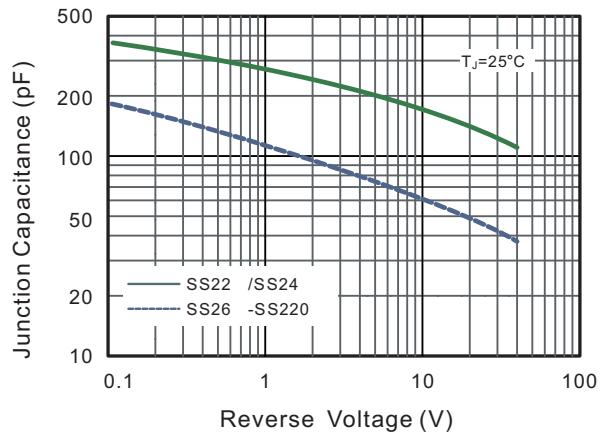


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

